5 é / Descriptions

SOT23-3 .> / / x P 3 « | • ’ož

6‑ CHANNEL MOSFET in a SOT23 -3 Plastic Package.

¤ ª / Features

V_{DS}=-60V; I_D=-3A

$R_{DS(on)1}$@-10V 0 100m ¡ (Type.83m ¡)

$R_{DS(on)2}$@-4.5V 0 130m ¡ (Type.100m ¡)

… ` ' +) 7 ö Õ ä U ´ Å } L k —)í D }ož

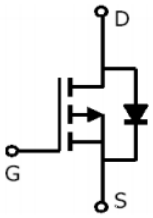
Qualified to AEC-Q101 Standards for High Reliability, HF Product.

Ð ÷ / Applications

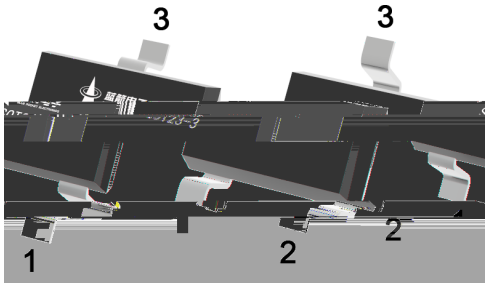
6 = 3 • ¿ ú • ¼ k á V ñ • } Lož

PWM application & Load switch, Meet the stringent requirements of automotive applications.

Ã W] Ô · / Equivalent Circuit



• Û - æ / Pinning



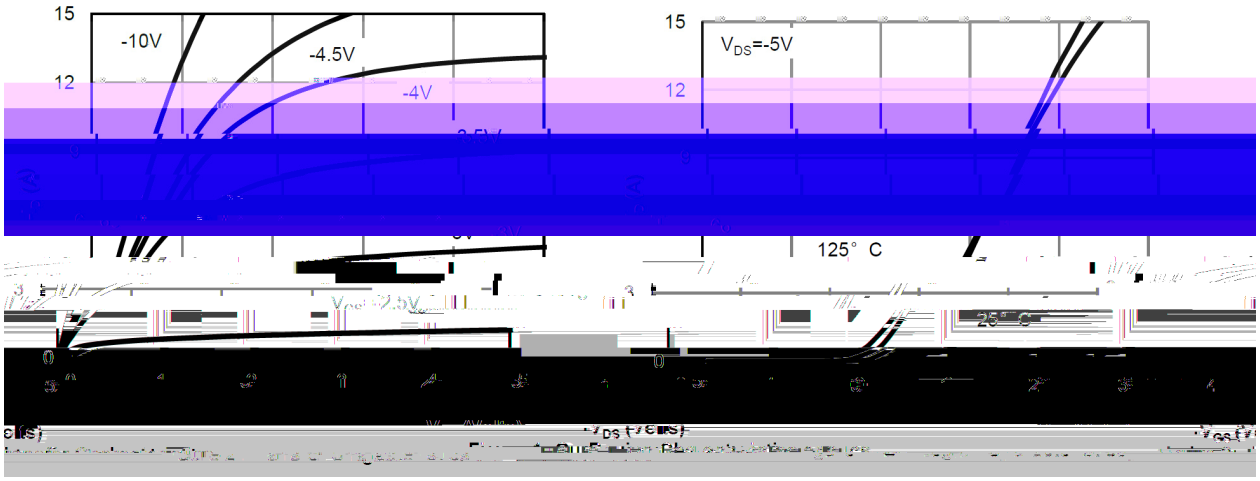
PIN1 y G PIN 2 y S PIN 3 y D

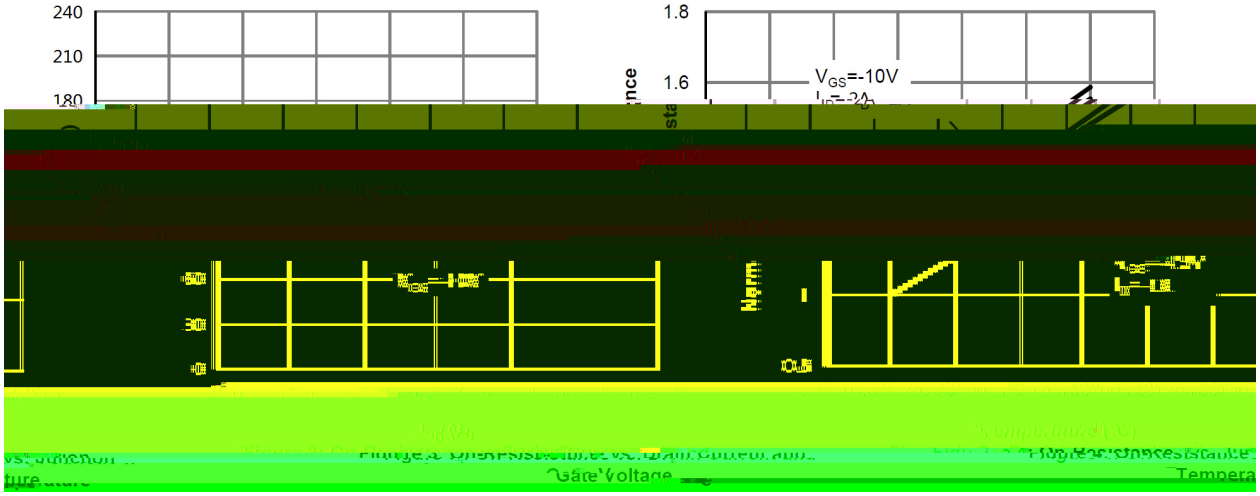
, M V / Marking

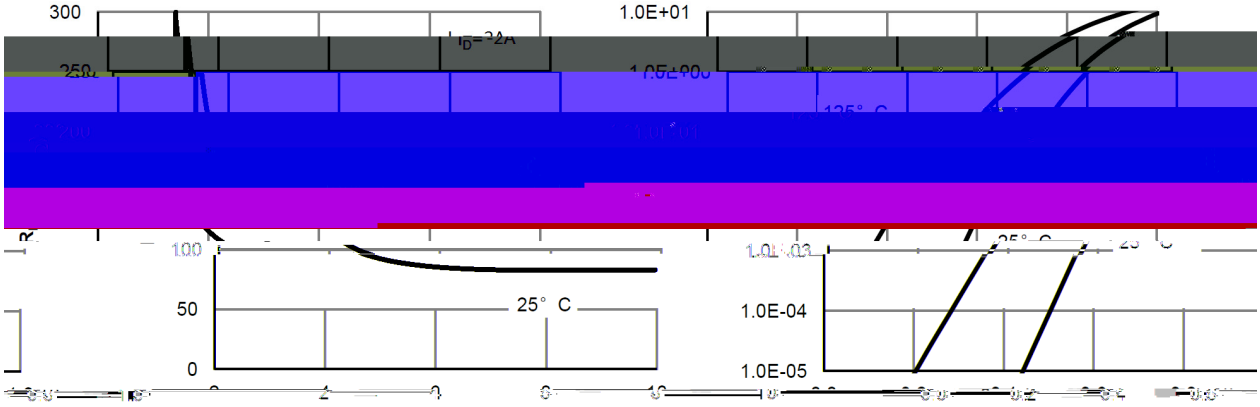
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See Marking Instructions.

Ô ? d • Ž ¢ / Electrical Characteristic Curve





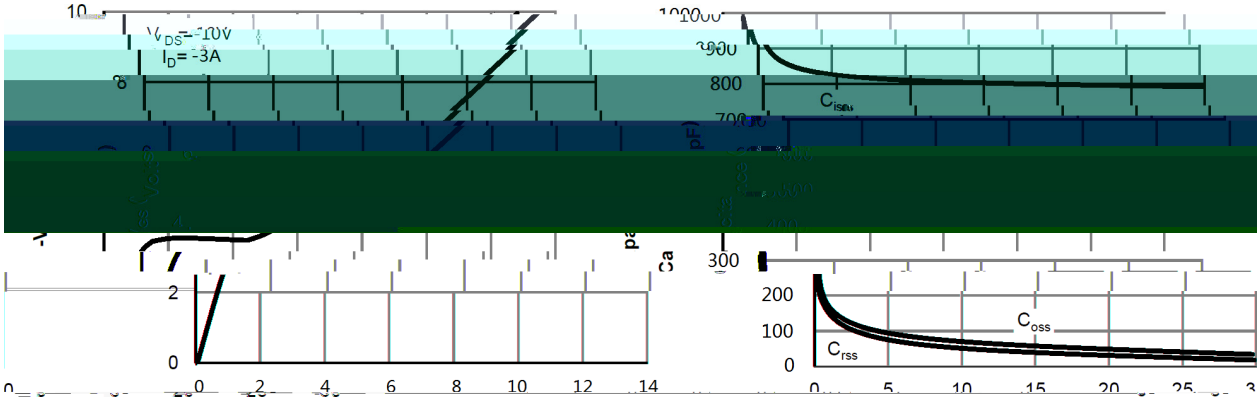


eristics

$-V_{GS}$ (Volts)
Figure 5: On-Resistance vs. Gate-Source Voltage

$-V_{SD}$ (Volts)
Figure 6: Body-Diode Charact

Ô ? d • Ž ¢ / Electrical Characteristic Curve



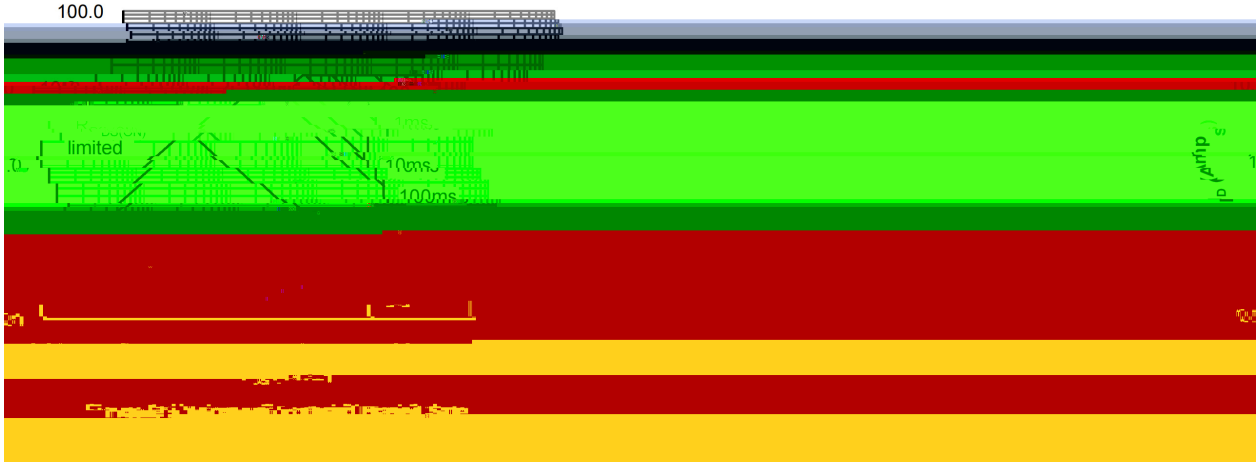
$-V_{DS}$ (Volts)

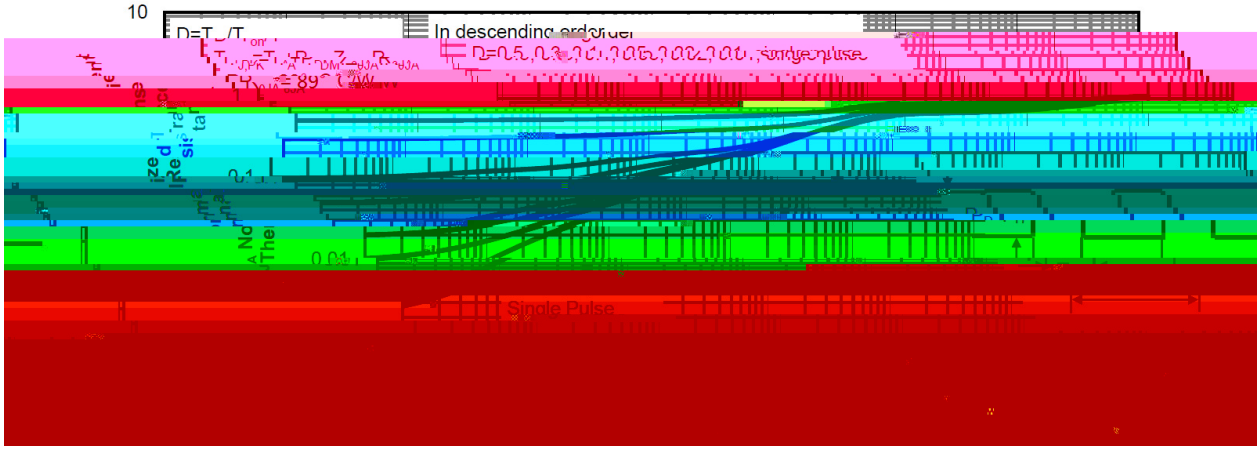
Capacitance Characteristics

Q_g (nC)

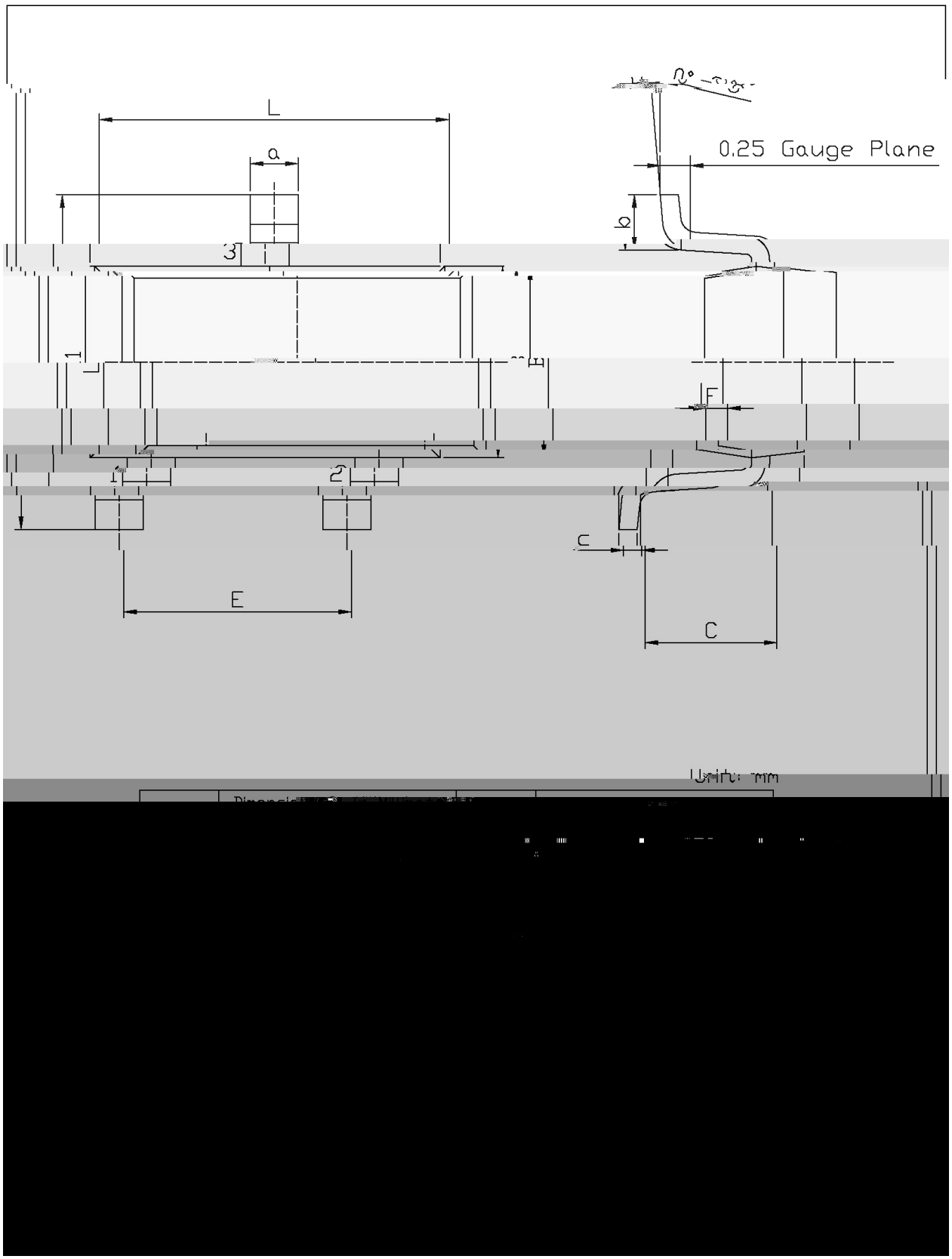
Figure 7: Gate-Charge Characteristics

Figure 8

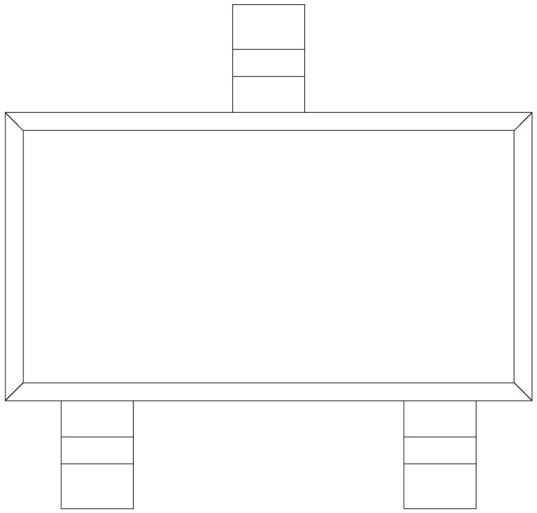




Ø ¤ =) ¢ / Package Dimensions



, M y ƒ / Marking Instructions



ª ¢ y

7 y V ñ —)í D } ö œ

C1 y

š WD t … • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6

ª ¢ y

1o• Ä ½ “ † 150 ½200 - k ž • 60 ½120sec;

2o• Q › “ † 255 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~200 - , Time:60~120sec.

2.Peak Temp.:255 r5 - , Duration:5 r0.5sec.

3.Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »] / Resistance to Soldering Heat Test Conditions

“ † y 260 r5 - ž • y 10 r1 sec. Temp.:260±5 Time:10±1 sec

á!De ‰Y™ á À ì ’ Ê "• Áƒ CĐ AHyƒq† y